

1. General description

Planar passivated high commutation three quadrant triac in a SOT404 (D2PAK) surface mountable plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity. The "sensitive gate" "series E" is intended for interfacing with low power drivers including microcontrollers.

2. Features and benefits

- 3Q technology for improved noise immunity •
- Direct interfacing with low power drivers and microcontrollers •
- Good immunity to false turn-on by dV/dt
- High commutation capability with sensitive gate •
- High voltage capability •
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Surface mountable package
- Triggering in three quadrants only

3. Applications

- Electronic thermostats (heating and cooling) •
- High power motor controls e.g. washing machines and vacuum cleaners •

4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 100 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	-	12	A
I _{TSM}	non-repetitive peak on- state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	-	100	A
		full sine wave; T _{j(init)} = 25 °C; t _p = 16.7 ms	-	-	110	A
Tj	junction temperature		-	-	125	°C
Static chara	acteristics					
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	2	-	10	mA

Table 1. Quick reference date

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	2	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	2	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	15	mA
V _T	on-state voltage	I _T = 15 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
Dynamic ch	naracteristics		· ·	·		
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	50	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T _j = 125 °C; I _{T(RMS)} = 12 A; dV _{com} /dt = 20 V/µs; (snubberless condition); gate open circuit	3	-	-	A/ms
		V_D = 400 V; T _j = 125 °C; I _{T(RMS)} = 12 A; dV _{com} /dt = 10 V/µs; gate open circuit	6	-	-	A/ms
		V_D = 400 V; T _j = 125 °C; I _{T(RMS)} = 12 A; dV _{com} /dt = 1 V/µs; gate open circuit	10	-	-	A/ms

5. Pinning information

Table 2. Pinning information

	3			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2-71
2	T2	main terminal 2		sym051
3	G	gate	ii	Symoor
mb	T2	mounting base; main terminal 2		
			D2PAK (SOT404)	

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BTA312B-800E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

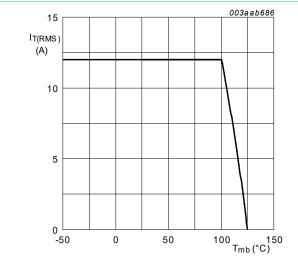


7. Limiting values

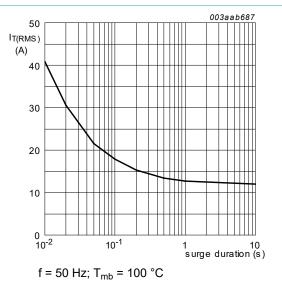
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 100 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	12	A
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	100	A
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	110	А
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	50	A²s
dl _T /dt	rate of rise of on-state current	I _G = 20 mA	-	100	A/µs
I _{GM}	peak gate current		-	2	А
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _i	junction temperature		-	125	°C

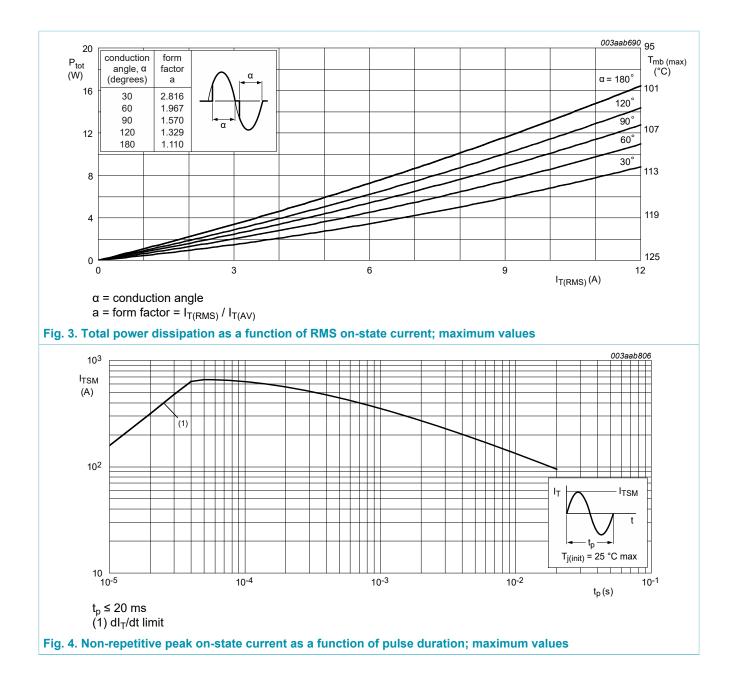






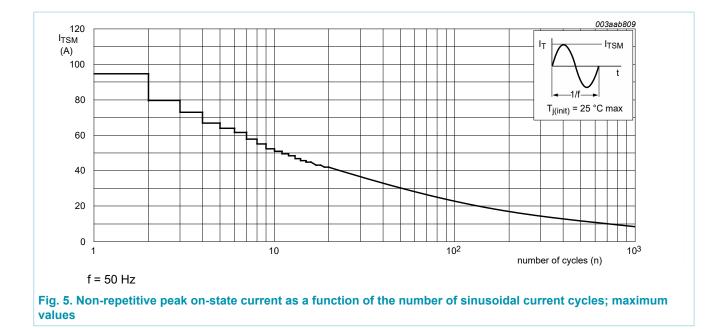


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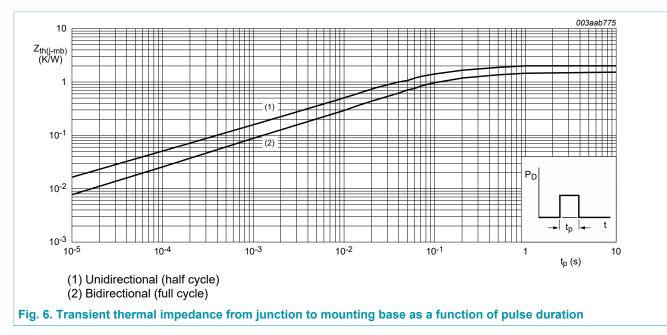
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8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	full cycle; <u>Fig. 6</u>	-	-	1.5	K/W
		half cycle; <u>Fig. 6</u>	-	-	2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	printed circuit board mounted; minimum footprint	-	55	-	K/W



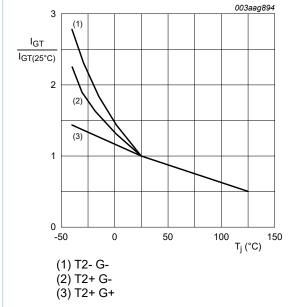
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9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	2	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	2	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	2	-	10	mA
ΙL	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	-	25	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 8</u>	-	-	30	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 8</u>	-	-	35	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	15	mA
V _T	on-state voltage	I _T = 15 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; <u>Fig. 11</u>	-	0.8	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; <u>Fig. 11</u>	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic ch	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	50	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	$\label{eq:VD} \begin{array}{l} V_D = 400 \text{ V}; T_j = 125 ^\circ\text{C}; I_{T(RMS)} = 12 \text{ A}; \\ dV_{com}/dt = 20 V/\mu\text{s}; (\text{snubberless} \\ \text{ condition}); \text{gate open circuit} \end{array}$	3	-	-	A/ms
		$\label{eq:VD} \begin{array}{l} V_D = 400 \; V; \; T_j = 125 \; ^\circ C; \; I_T(RMS) = 12 \; A; \\ dV_com/dt = 10 \; V/\mus; \; gate \; open \; circuit \end{array}$	6	-	-	A/ms
		V_D = 400 V; T _j = 125 °C; I _{T(RMS)} = 12 A; dV _{com} /dt = 1 V/µs; gate open circuit	10	-	-	A/ms

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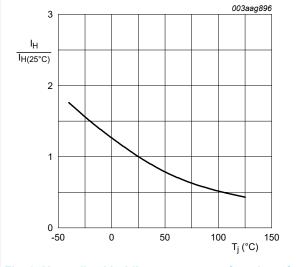
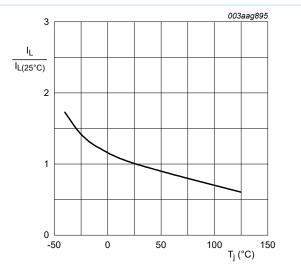
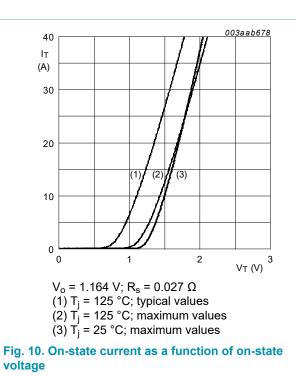


Fig. 9. Normalized holding current as a function of junction temperature

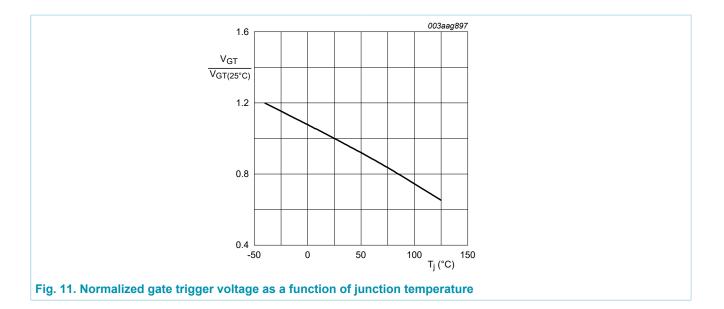






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10. Package outline

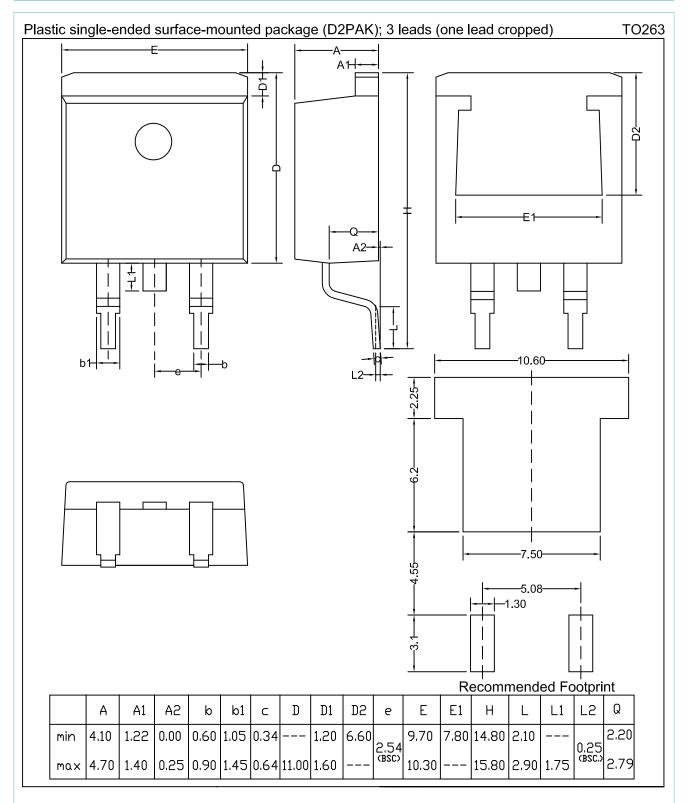


Fig. 12. Package outline D2PAK (SOT404)

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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